STARPOWER

SEMICONDUCTOR™

IGBT

GD300HTL120C7S

Preliminary

Molding Type Module

1200V/300A 6 in one-package

General Description

STARPOWER IGBT power module provides ultra low conduction loss as well as short circuit ruggedness. They are designed for the applications such as general inverters and UPS.



Features

- Low V_{CE(sat)} SPT+ IGBT technology
- Low switching losses
- 10µs short circuit capability
- Square RBSOA
- V_{CE(sat)} with positive temperature coefficient
- Low inductance case
- Fast & soft reverse recovery anti-parallel FWD
- Isolated copper baseplate using DBC technology

Typical Applications

- Inverter for motor drive
- AC and DC servo drive amplifier
- Uninterruptible power supply

IGBT-inverter $T_C=25$ °C unless otherwise noted

Maximum Rated Values

Symbol	Description	GD300HTL120C7S	Units	
V _{CES}	Collector-Emitter Voltage @ T _j =25°C	1200	V	
V_{GES}	Gate-Emitter Voltage	±20	V	
$I_{\rm C}$	Collector Current @ $T_C=25^{\circ}C$	560	Α.	
	@ T _C =100℃	300	A	
I_{CM}	Pulsed Collector Current t _p =1ms	600	A	
P _{tot}	Total Power Dissipation @ T _j =175°C	2206	W	

Off Characteristics

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Units
V _{(BR)CES}	Collector-Emitter	T:=25°C 1200		V		
	Breakdown Voltage	$T_{j}=25^{\circ}C$	1200			·
I _{CES}	Collector Cut-Off Current	$V_{\text{CE}}=V_{\text{CES}}, V_{\text{GE}}=0V,$			5.0	mA
		T _j =25℃				
I_{GES}	Gate-Emitter Leakage	$V_{GE}=V_{GES},V_{CE}=0V,$			400	A
	Current	T _j =25℃			400	nA

On Characteristics

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Units
$V_{\text{GE(th)}}$	Gate-Emitter Threshold	$I_{C}=12\text{mA}, V_{CE}=V_{GE},$	5.0 6.2		7.0	V
	Voltage	$T_j=25^{\circ}C$	3.0	0.2	7.0	·
V _{CE(sat)}		$I_{C}=300A, V_{GE}=15V,$		1.90	2.35	
	Collector to Emitter Saturation Voltage	T _j =25℃				N/
		$I_{C}=300A, V_{GE}=15V,$		2.10		·
		T _j =125℃				

Switching Characteristics

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Units
Q_{G}	Gate charge	V _{GE} =-15+15V		3.2		μC
\mathbf{E}_{on}	Turn-On Switching Loss	V_{CC} =600V, I_{C} =300A, R_{G} =3.3 Ω , V_{GE} = \pm 15V, T_{j} =25 $^{\circ}$ C		32		mJ
$E_{ m off}$	Turn-Off Switching Loss			19		mJ
E _{tot}	Total Switching Loss			51		mJ
Eon	Turn-On Switching Loss	V _{CC} =600V,I _C =300A,		43		mJ
$E_{ m off}$	Turn-Off Switching Loss	$R_{G}=3.3\Omega, V_{GE}=\pm 15V,$ $T_{j}=125^{\circ}C$		32		mJ
E _{tot}	Total Switching Loss			75		mJ

t _{d(on)}	Turn-On Delay Time	V COOM 2004	135	ns
t _r	Rise Time	$V_{CC}=600V,I_{C}=300A,$	65	ns
t _{d(off)}	Turn-Off Delay Time	$R_{G}=3.3\Omega, V_{GE}=\pm 15V,$	425	ns
$t_{\rm f}$	Fall Time	$T_{\rm j}$ =25°C	55	ns
t _{d(on)}	Turn-On Delay Time	V COOM 200 A	150	ns
t _r	Rise Time	V _{CC} =600V,I _C =300A,	65	ns
$t_{ m d(off)}$	Turn-Off Delay Time	R_G =3.3Ω, V_{GE} =±15V, T_j =125 °C	485	ns
$t_{\rm f}$	Fall Time		75	ns
Cies	Input Capacitance		22.3	nF
Coes	Output Capacitance	$V_{CE}=25V, f=1Mhz,$	1.56	nF
C _{res}	Reverse Transfer Capacitance	$V_{GE}=0V$	1.02	nF
I_{SC}	SC Data	$t_{SC} \leq 10 \mu s, V_{GE} \leq 15 \text{ V},$ $T_j = 125 ^{\circ}\text{C}, V_{CC} = 600 \text{V},$ $V_{CEM} \leq 1200 \text{V}$	1500	A
R _{Gint}	Internal Gate Resistance		0.7	Ω

$\textbf{DIODE-inverter} \ \, T_{C}\!\!=\!\!25\,^{\circ}\!\text{C unless otherwise noted}$

Maximum Rated Values

Symbol	Description	GD300HTL120C7S	Units
V_{RRM}	Collector-Emitter Voltage @ T _j =25°C	1200	V
I_{F}	DC Forward Current @ T _C =80°C	300	A
I _{FRM}	Repetitive Peak Forward Current t _p =1ms	600	A

Characteristics Values

Symbol	Parameter	Test Condit	Test Conditions		Тур.	Max.	Units
* 7	Diode Forward	I -200 A W -0W	T _j =25℃		1.80	2.20	V
V_{F}	Voltage	$I_F = 300A, V_{GE} = 0V$	T _j =125℃		1.85]
Qr	D 1.Cl		T _j =25℃		39		C
	Recovered Charge	$V_{R}=600 V_{r}$	T _j =125℃		75		μC
т	Peak Reverse	$I_{F}=300A,$	T _j =25℃		249		A
I_{RM}	Recovery Current	$R_G=3.3\Omega$,	T _j =125℃		330		A
Б	Reverse Recovery	$V_{GE}=-15V$	T _j =25℃		14		Т
E _{rec}	Energy		T _j =125℃		30		mJ

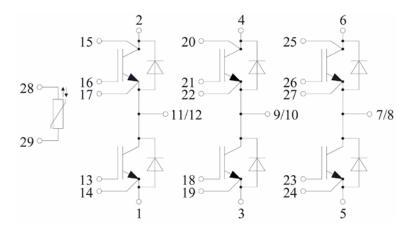
Electrical Characteristics of NTC $T_C=25$ °C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Units
R ₂₅	Rated Resistance			5.0		kΩ
$\Delta R/R$	Deviation of R ₁₀₀	$T_{C}=100^{\circ}C, R_{100}=493.3\Omega$	-5		5	%
P ₂₅	Power Dissipation				20.0	mW
B _{25/50}	B-value	R ₂ =R ₂₅ exp[B _{25/50} (1/T ₂ -1/(298.1 5K))]		3375		K

IGBT Module

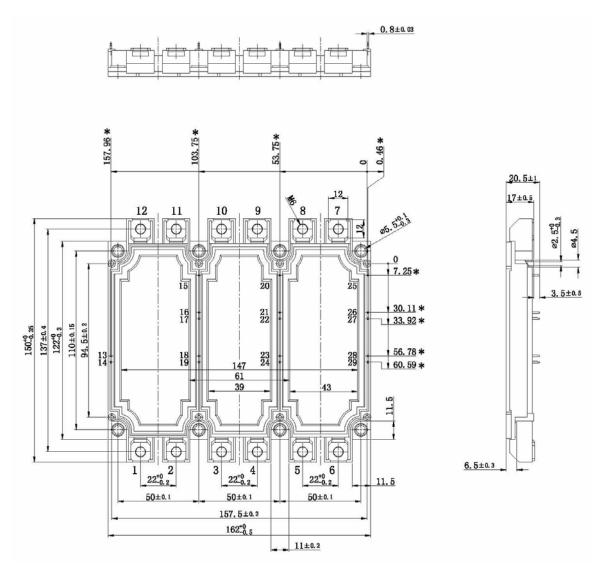
Symbol	Parameter	Min.	Тур.	Max.	Units
V_{ISO}	Isolation Voltage RMS,f=50Hz,t=1min		2500		V
L_{CE}	Stray Inductance		20		nН
$R_{CC^{'}+EE^{'}}$	Module Lead Resistance, Terminal to Chip @ $T_C=25^{\circ}C$		1.1		mΩ
$R_{ heta JC}$	Junction-to-Case (per IGBT)			0.068	W/W
	Junction-to-Case (per DIODE)			0.116	K/W
$R_{\theta CS}$	Case-to-Sink (Conductive grease applied)		0.005		K/W
T_{jmax}	Maximum Junction Temperature			175	$^{\circ}\!\mathbb{C}$
T_{STG}	Storage Temperature Range	-40		125	$^{\circ}\!\mathbb{C}$
Mounting	Power Terminal Screw:M5	3.0		6.0	N.m
Torque	Mounting Screw:M6	3.0		6.0	N.m
Weight	Weight of Module		910		g

Equivalent Circuit Schematic



Package Dimension

Dimensions in Millimeters



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